SGS-THOMSON MICROELECTRONICS

74LCX646

PRELIMINARY DATA

LOW VOLTAGE CMOS OCTAL BUS TRANSCEIVER/REGISTER WITH 5V TOLERANT INPUTS AND OUTPUTS

- 5V TOLERANT INPUTS AND OUTPUTS
- HIGH SPEED: t_{PD} = 7.0 ns (MAX.) at V_{CC} = 3V
- POWER-DOWN PROTECTION ON INPUTS AND OUTPUTS
- SYMMETRICAL OUTPUT IMPEDANCE: |I_{OH}| = I_{OL} = 24 mA (MIN)
- PCI BUS LEVELS GUARANTEED AT 24mA
- BALANCED PROPAGATION DELAYS: tPLH ≅ tPHL
- OPERATING VOLTAGE RANGE:
 V_{CC} (OPR) = 2.0V to 3.6V (1.5V Data Retention)
- PIN AND FUNCTION COMPATIBLE WITH 74 SERIES 646
- LATCH-UP PERFORMANCE EXCEEDS 500mA
- ESD PERFORMANCE: HBM >2000V; MM > 200V

DESCRIPTION

The LCX646 is a low voltage CMOS OCTAL BUS TRANSCEIVER AND REGISTERS (3-STATE) fabricated with sub-micron silicon gate and double-layer metal wiring C^2MOS technology. It is ideal for low power and high speed 3.3V applications; it can be interfaced to 5V signal enviroment for both inputs and outputs.

PIN CONNECTION AND IEC LOGIC SYMBOLS



This device consist of bus transceiver circuits with 3-state output, D type flip-flops, and control circuitry arranged for multiplexed trasmission of data directly from the input bus or from the internal registers. Data on the A or B bus will be clocked into registers on the low-to high transition of the appropriate clock pin (clock AB or clock BA). Enable (\overline{G}) and direction (DIR) pins are provided to control the transceiver functions. In the transceiver mode, data present at the high impedance port may be stored in either register or in both.

The selected controls (Select AB select BA) can multiplex stored and real time (transparent mode) data. The direction control determines which bus



will receive data when enable \overline{G} is active (low).

In the isolation mode (enable \overline{G} high), "A" data may be stored in one register and/or "B" data may be stored in the other register. When an output bus is disabled, the input bus is still enabled and may be used to store and transmit data. Only one of the two buses, A or B, may be driven at a time. It has same speed performance at 3.3V than 5V, AC/ACT family, combined with a lower power consumption.

All inputs and outputs are equipped with protection circuits against static discharge, giving them 2KV ESD immunity and transient excess voltage.

INPUT AND OUTPUT EQUIVALENT CIRCUIT



PIN DESCRIPTION

PIN No	SYMBOL	NAME AND FUNCTION
1	CAB	A to B Clock Input (LOW to HIGH, Edge-Trigged)
2	SAB	Select A to B Source Input
3	GAB	Direction Control Input
4, 5, 6, 7, 8, 9, 10, 11	A1 to A8	A Data Inputs/Outputs
20, 19, 18, 17, 16, 15, 14, 13	B1 to B8	B Data Inputs/Outputs
21	G	Output Enable Input (Active LOW)
22	SBA	Select B to A Source Input
23	CBA	B to A Clock Input (LOW to HIGH, Edge-Triggered)
12	GND	Ground (0V)
24	V _{CC}	Positive Supply Voltage



LOGIC DIAGRAM



TIMING CHART





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TRUTH TABLE

G	DIR	САВ	СВА	SAB	SBA	Α	В	FUNCTION
						INPUTS	INPUTS	Both the A bus and the B bus are inputs
	V	Х	Х	Х	Х	Z	Z	The output functions of the A and B bus are disabled
н	X			Х	Х	INPUTS	INPUTS	Both the A and B bus are used as inputs to the internal flip-flops. Data on the bus will be stored on low to high transition of the clock inputs
						INPUTS	OUTPUTS	The A bus are inputs and the B bus are outputs
		X	X*	L	Х	L	L	The data at the A bus are displayed on the B bus
						Н	Н	
			X*	L	Х	L	L	The data on the A bus are displayed on the B bus.
L	н					Н	Н	The data on the A bus are stored in the A internal flip-flop on low to high transition of th clock pulse.
		Х	Х*	н	Х	Х	Qn	The data stored to the internal flip-flop are dispayed on the B bus
			X*	Н	Х	L	L	The data on the A bus are stored in the A internal
						Н	Н	flip-flop on low to high transition of the clock pulse. The states of the A internal flip-flops propagate directly to the B bus
						OUTPUTS	INPUTS	The B bus are inputs and the A bus are outputs
		X*	x	x		L	L	The data on the B bus are displayed on the A bus
				~	_	Н	Н	
		X*		Х	L	L	L	The data on the B bus are displayed on the A bus.
L	L					Н	Н	The data on the B bus are stored on the B internal flip-flop on low to high transition of the clock pulse
		Х*	Х	Х	н	Qn	Х	The data stored in the B internal flip-flops are displayed on the A bus
		x*		Х	Н	L	L	the data on the B bus are stored in the B internal flip-
						Н	Н	flop on low to high transition of the clock pulse. The states of the B internal flip-flops propagate output directly to the A bus

X DON'T CARE Z HIGH IMPEDANCE

Qn : THE DATA STORED TO THE INTERNAL FLIP-FLOPS BY MOST RECENT LOW TO HIGH TRANSITION OF THE CLOCK INPUTS *

: THE DATA AT THE A AND B BUS WILL BE STORED TO THE INTERNAL FLIP-FLOPS ON EVERY LOW TO HIGH TRANSITION OF THE CLOCK INPUTS



ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter	Value	Unit
Vcc	Supply Voltage	-0.5 to + 7.0	V
VI	DC Input Voltage	-0.5 to + 7.0	V
Vo	DC Output Voltage (Vcc=0V)	-0.5 to + 7.0	V
Vo	DC Output Voltage (High or Low State) (note1)	-0.5 to V _{CC} + 0.5	V
Іік	DC Input Diode Current	- 50	mA
Іок	DC Output Diode Current (note2)	± 50	mA
lo	DC Output Source/Sink Current	± 50	mA
Icc	DC Supply Current per Supply Pin	± 100	mA
	DC Ground Current per Supply Pin	± 100	mA
T _{stg}	Storage Temperature	-65 to +150	°C
TL	Lead Temperature (10 sec)	300	°C

Absolute Maximum Ratings are those values beyond which damage to the device may occur. Functional operation under these condition is not implied. 1) Io absolute maximum rating must be observed 2) $V_0 < GND, V_0 > V_{CC}$

RECOMMENDED OPERATING CONDITIONS

Symbol	Parameter	Value	Unit
V _{CC}	Supply Voltage (note 1)	2.0 to 3.6	V
VI	Input Voltage	0 to 5.5	V
Vo	Output Voltage (V _{CC} =0V)	0 to 5.5	V
Vo	Output Voltage (High or Low State)	0 to V _{CC}	V
I _{OH} , I _{OL}	High or Low Level Output Current (V _{CC} = 3.0 to 3.6V)	± 24	mA
I _{OH} , I _{OL}	High or Low Level Output Current (V _{CC} = 2.7 to 3.0V)	± 12	mA
T _{op}	Operating Temperature:	-40 to +85	°C
dt/dv	Input Transition Rise or Fall Rate ($V_{CC} = 3.0V$) (note 2)	0 to 10	ns/V

1) Truth Table guaranteed: 1.5V to 3.6V

2) V_{IN} from 0.8V to 2.0V



DC SPECIFICATIONS

Symbol	Parameter	Test	Condit	ions	Va	lue	Unit
		Vcc			-40 to	85 °C	
		(V)			Min.	Max.	
VIH	High Level Input Voltage	27 to 36			2.0		V
VIL	Low Level Input Voltage	2.7 10 5.0				0.8	V
V _{OH}	High Level Output Voltage	2.7 to 3.6	V	I _O =-100 μA	V _{CC} -0.2		
		2.7	ViH or	I ₀ =-12 mA	2.2		v
		3.0	VIL	I _O =-18 mA	2.4		
		5.0		I ₀ =-24 mA	2.2		
Vol	Low Level Output Voltage	2.7 to 3.6	V	l _O =100 μA		0.2	
		2.7	VIH or	I _O =12 mA		0.4	v
		3.0	VIL	I _O =16 mA		0.4	
		3.0		I ₀ =24 mA		0.55	
h	Input Leakage Current	2.7 to 3.6	V1 =	0 to 5.5 V		±5	μA
loz	3 State Output Leakage Current	2.7 to 3.6	V _I = V _O =	V _{IH} or V _{IL} 0 to 5.5V		±5	μA
l _{off}	Power Off Leakage Current	0	V _I or '	Vo = 5.5V		100	μA
Icc	Quiescent Supply Current	2.7 to 3.6	Vi = V	Cc or GND		10	
			V _I 3.6	or V _O = to 5.5V		±10	μA
Δlcc	ICC incr. per input	2.7 to 3.6	VIH =	V _{CC} -0.6V		500	μA

DYNAMIC SWITCHING CHARACTERISTICS

Symbol	Parameter	Test Conditions		Value			Unit
		Vcc		Т	a = 25 °	°C	
		(V)		Min.	Тур.	Max.	
V _{OLP}	Dynamic Low Voltage Quiet Output	3.3	C _L = 50 pF		0.8		
Volv	(note 1)		V _{IL} = 0 V V _{IH} = 3.3V		-0.8		V

1) Number of outputs defined as "n". Measured with "n-1" outputs switching from HIGH to LOW or LOW to HIGH. The remaining output is measured in the LOW state.



Symbol	Parameter	Test	Va	Unit		
		Vcc	Waveform	-40 to	85 °C	
		(V)		Min.	Max.	
t _{PLH}	Propagation_Delay Time	2.7	4	1.5	9.5	50
t _{PHL}	CK to Q or \overline{Q}	3.0 to 3.6		1.5	8.5	115
t _{PLH}	Propagation Delay Time	2.7	4	1.5	8.0	ns
t _{PHL}	An or Bn to Q or \overline{Q}	3.0 to 3.6		1.5	7.0	
t _{PLH}	Propagation Delay Time	2.7	4	1.5	9.5	20
t _{PHL}	SELECT to Q or \overline{Q}	3.0 to 3.6		1.5	8.5	115
t _{PZL}	Output Enable Time	2.7	2	1.5	9.5	ns
t _{PZH}		3.0 to 3.6	2	1.5	8.5	
t _{PLZ}	Output Disable Time	2.7	2	1.5	9.5	ns
t _{PHZ}		3.0 to 3.6	2	1.5	8.5	
ts	Setup Time, HIGh or LOW Level Data	2.7	1	2.5		ne
	to Ck	3.0 to 3.6		2.5		115
t _h	Hold Time, HIGh or LOW Level Data to	2.7	1	1.5		nc
	Ck	3.0 to 3.6		1.5		115
tw	CK Pulse Width, HIGH or LOW	2.7	3	4.0		ne
		3.0 to 3.6	5	3.3		115
f _{MAX}	Clock Pulse Frequency	3.0 to 3.6	1	150		MHz
tos∟z t _{OSHL}	Output to Output Skew Time (note 1, 2)	3.0 to 3.6			1.0	ns

AC ELECTRICAL CHARACTERISTICS ($C_L = 50 \text{ pF}$, $R_L = 500 \Omega$, Input $t_r = t_f = 2.5 \text{ ns}$)

1) Skew is defined as the absolute value of the difference between the actual propagation delay for any two outputs of the same device switching in the same direction, either HIGH or LOW ($t_{OSLH} = |t_{PLHm} - t_{PLHn}|, t_{OSHL} = |t_{PHLm} - t_{PHLn}|$) 2) Parameter guaranteed by design

CAPACITIVE CHARACTERISTICS

Symbol	Parameter	Test Conditions			Value		Unit
		V _{cc}		T,	a = 25 °	°C	
		(V)		Min.	Тур.	Max.	
CIN	Input Capacitance	3.3	$V_{IN} = 0$ to V_{CC}		6		pF
Ci/o	I/O Capacitance	3.3	$V_{IN} = 0$ to V_{CC}		10		рF
CPD	Power Dissipation Capacitance (note 1)	3.3	f _{IN} = 10MHz V _{IN} = 0 or V _{CC}		TBD		pF

1) C_{PD} is defined as the value of the IC's internal equivalent capacitance which is calculated from the operating current consumption without load. Average operting current can be obtained by the following equation. $I_{CC}(opr) = C_{PD} \bullet V_{CC} \bullet f_{IN} + I_{CC}/n$ (per circuit)



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TEST CIRCUIT



 $C_L = 50 \text{ pF}$ or equivalent (includes jig and probe capacitance)

 $\begin{array}{l} R_L = R_1 = 500 \Omega \text{ or equivalent} \\ R_T = Z_{OUT} \text{ of pulse generator (typically 50 \Omega)} \end{array}$

WAVEFORM 1: PROPAGATION DELAYS, SAB, SBA, An, Bn TIMES (f=1MHz; 50% duty cycle)







WAVEFORM 2: OUTPUT ENABLE AND DISABLE TIMES (f=1MHz; 50% duty cycle)





WAVEFORM 3: PROPAGATION DELAY TIMES (f=1MHz; 50% duty cycle)

WAVEFORM 4: PULSE WIDTH



DIM		mm		inch			
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.	
А			2.65			0.104	
a1	0.10		0.20	0.004		0.007	
a2			2.45			0.096	
b	0.35		0.49	0.013		0.019	
b1	0.23		0.32	0.009		0.012	
С		0.50			0.020		
c1			45 ((typ.)			
D	15.20		15.60	0.598		0.614	
E	10.00		10.65	0.393		0.420	
е		1.27			0.05		
e3		13.97			0.55		
F	7.40		7.60	0.291		0.299	
L	0.50		1.27	0.19		0.050	
S			8 (n	nax.)			

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DIM.		mm		inch			
2	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.	
А			1.1			0.433	
A1	0.05	0.10	0.15	0.002	0.004	0.006	
A2	0.85	0.9	0.95	0.335	0.354	0.374	
b	0.19		0.30	0.0075		0.0118	
С	0.09		0.2	0.0035		0.0079	
D	7.7	7.8	7.9	0.303	0.307	0.311	
Е	6.25	6.4	6.5	0.246	0.252	0.256	
E1	4.3	4.4	4.48	0.169	0.173	0.176	
е		0.65 BSC			0.0256 BSC		
К	0°	4°	8 ⁰	0°	4°	8°	
L	0.50	0.60	0.70	0.020	0.024	0.028	





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